IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Serial No.: Group Art Unit:

Inventors: Belov et al. Filed:

Title: High Selectivity Colloidal Silica Slurry Examiner:

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with 37 CFR 1.51, 1.56 and 1.97 to 1.99, the list of references cited on the attached Form PTO-1449 is made of record to assist the Patent and Trademark Office in its examination of this application. A copy of each of the references cited is enclosed herewith. Since we have not received an Office Action on the merits, no fee is believed to be due.

This disclosure statement should neither be construed as a representation that a search has been made, nor as an admission that the information cited is, or is considered to be, material to patentability as defined in 1.56(b).

Respectfully submitted,

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Date: November 19, 2003

Form PTO-1449 (Rev. 8-83) U.S. Department of Commerce	Atty. Docket No. D-21,389	Serial No.
Information Disclosure Citation (Use several sheets if necessary)	Applicants Belov et al.	
	Filing Date	Group

U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
		4 5 2 5 6 3 1	6/1985	Allison	290	4	
		5 6 7 1 8 5 1	9/1997	Johnson et al.	211	51	
		5 7 3 8 8 0 0	4/1998	Hosali et al.	216	99	
		5 7 5 9 9 1 7	6/1998	Grover et al.	438	690	
		6 0 1 9 8 0 6	2/2000	Sees et al.	51	308	
		6 0 4 2 7 4 1	3/2000	Hosali et al.	252	79.1	
		6 1 1 4 2 4 9	9/2000	Canaperi et al.	438	692	
		6 1 3 2 6 3 7	10/2000	Hosali et al.	252	79.1	
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Other Documents (including Author, Title, Date, Pertinent Pages, Etc.)

			Cook, "Chemical Processes in Glass Polishing", Journal of Non-Crystalline Solids (1990) pp 152-171
			Lo et al, "Characterization of Selective-CMP, Dummy Pattern and Reverse Mask Approaches in STI Planarization Process", Proceedings of 1999 CMP-MIC, pp-333-335
			Lee et al., "The Effects of Slurries with Pattern Size and Step Height in Shallow Trench Isolation Chemical Mechanical Polishing", Proceedings of 2000 CMP-MIC, pp 288-290
			Jin et al., "Advanced Front End CMP and Integration Solutions", Proceedings of 2000 CMP-MIC, pp 119-129
			Bonner et al., "Development of a Direct Polish Process for Shallow Trench Isolation Modules", Proceedings of 2001 CMP-MIC, pp. 572-579
			Xiao, "Introduction to Semiconductor Manufacturing Technology", Prentice-Hall Inc. (2001) pp. 384

Examiner	Date Considered

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		6 4 3 6 0 3 5	8/2002	Kido et al.	438	693	
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			Bonner et al, "Improved Direct Polish STI CMP Process with High Selectivity Slurry:Reduced Microscratching & Increased Productivity", Proceedings of 2002 CMP-MIC, pp 247-254
			Garliardi et al, "Fixed Abrasives and Selective Chemistries:Some Real Advantages for Direct STI CMP", Proceedings of 2002 CMP-MIC, pp 288-290
			Tseng et al., "STI CMP Process with High – Selectivity Slurry", Proceedings of 2002 CMP-MIC, pp. 255-259
			Leduc et al, "CMP:Aiming for Perfect Planarization", Proceedings of 2002 CMP-MIC, pp 239-246
			Devriendt et al, "Challenges for the Integration of Shallow Trench Isolation", Proceedings of 2003 CMP-MIC, pp 492-500

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			Nickles et al., "Meeting the Challenges of STI CMP", Nanochip Technology Journal (2003) pp. 42-45
			Lampara et al., "A High Oxide – Nitride Selectivity CMP Slurry for Shallow Trench Isolation", Electrochemical Society Proceedings, Vol. 98-7, pp 218-234

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